Power MOSFET for 3-Cells Lithium-ion Battery Protection 30 V, 6.5 mΩ, 19 A, Dual N-Channel, WLCSP6

This N-Channel Power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and ultra low on resistance.

This device is suitable for applications of Notebook PC.

Features

- Ultra Low On-Resistance
- Low Gate Charge
- Common-Drain type
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

• 3-Cells Lithium-ion Battery Charging and Discharging Switch

SPECIFICATIONS

ABSOLUTE MAXIMUM RATINGS at T_A = 25°C(Note 1)

Parameter	Symbol	Value	Unit
Source to Source Voltage	V _{SSS}	30	V
Gate to Source Voltage	V _{GSS}	±20	V
Source Current (DC)	۱ _S	19	А
Source Current (Pulse) PW ≤ 10 μs, duty cycle ≤ 1%	I _{SP}	76	A
Total Dissipation (Note 2)	PT	2.5	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient (Note 1)	$R_{\theta JA}$	50	°C/W

1. Surface mounted on ceramic substrate(5000 mm² \times 0.8 mm).

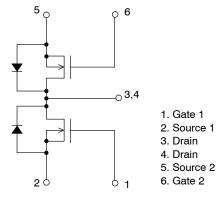


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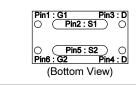
www.onsemi.com

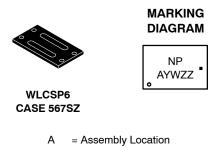
V _{SSS}	R _{SS(on)} Max	I _S Max
	6.5 mΩ @ 10 V	
30 V	8.4 mΩ @ 8 V	19 A
	13 mΩ @ 4.5 V	

ELECTRICAL CONNECTION N-CHANNEL



PIN ASSIGNMENT





- Y = Year
- W = Work Week
- ZZ = Assembly Lot
- = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS at T_A = 25°C (Note 1)

				Value		
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Source to Source Breakdown Voltage	V(_{BR}) _{SSS}	$I_{S} = 1 \text{ mA}, V_{GS} = 0 \text{ V}$	30			V
Zero-Gate Voltage Source Current	I _{SSS}	$V_{SS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	μA
Gate to Source Leakage Current	I _{GSS}	$V_{GS} = 20 \text{ V}, \text{ V}_{SS} = 0 \text{ V}$			200	nA
Gate Threshold Voltage	V _{GS} (th)	V _{SS} = 10 V, I _S = 1 mA	1.3		2.2	V
Static Source to Source On-State Re- sistance	R _{SS} (on)	V _{GS} = 10 V, I _S = 5 A	3.7	5.0	6.5	mΩ
		V _{GS} = 8 V, I _S = 5 A	4.0	5.3	8.4	mΩ
		V _{GS} = 4.5 V, I _S = 5 A	5.5	7.3	13	mΩ
Turn-ON Delay Time	t _d (on)	V _{SS} = 15 V, V _{GS} = 10 V		2.7		μs
Rise Time	t _r	I _S = 5 A, Rg = 5 kΩ Switching Test Circuit		2.0		μs
Turn-OFF Delay Time	t _d (off)			26		μs
Fall Time	t _f	1		5.7		μs
Total Gate Charge	Qg	V_{SS} = 15 V, V_{GS} = 4.5 V I_S = 5 A		18		nC
Forward Source to Source Voltage	V _{F(S-S)}	$I_S = 5 \text{ A}, V_{GS} = 0 \text{ V}, \text{ Power Time} = 1 \text{ ms}$		0.75	1.2	V

2. Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

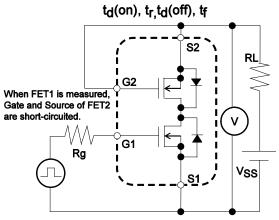
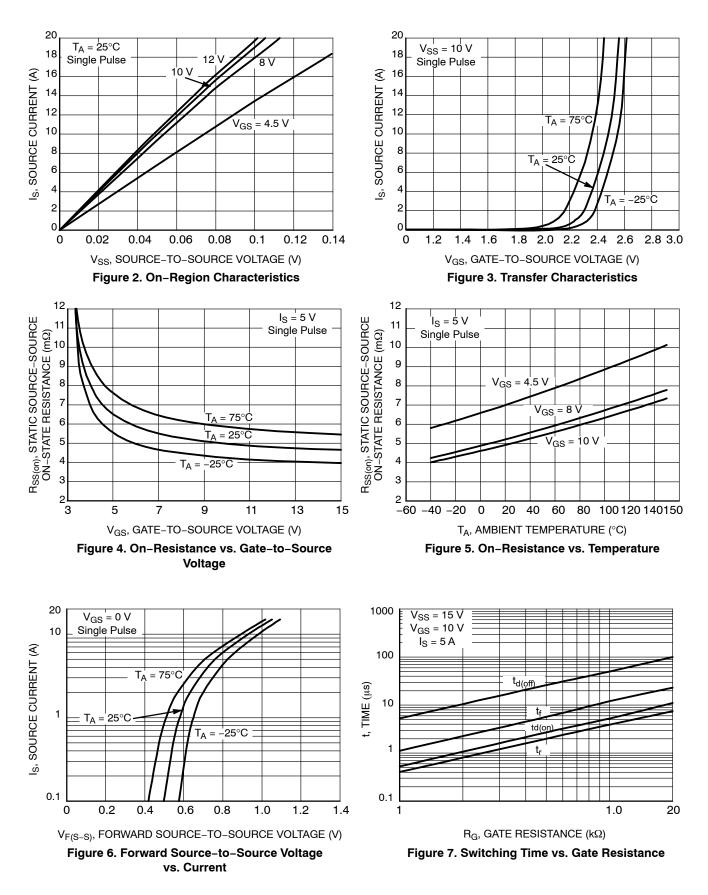


Figure 1. Switching Test Circuit

TYPICAL CHARACTERISTICS



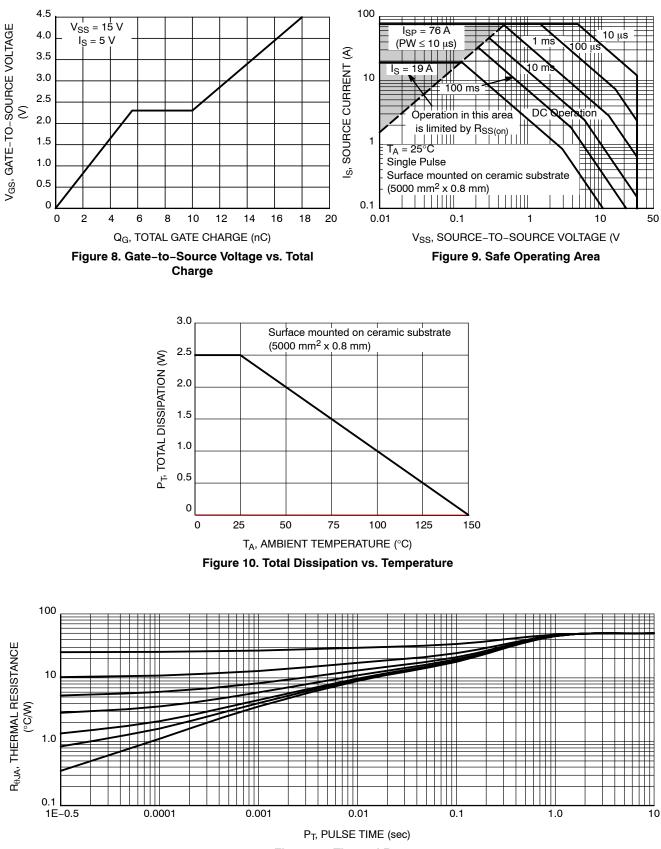


Figure 11. Thermal Response

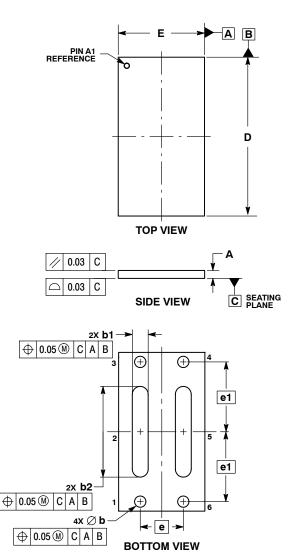
ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing) †
EFC4C012NLTDG	NP	WLCSP6 3.5x1.9x0.21 (Pb-Free / Halogen Free)	5000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

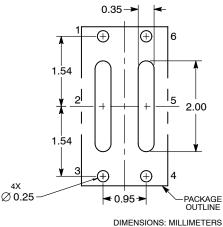
WLCSP6 3.5x1.9x0.21 CASE 567SZ **ISSUE A**



NOTES:
1. DIMENSIONING AND TOLERANCING PER
ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
Α	0.19	0.21	0.23
b	0.22	0.25	0.28
b1	0.32	0.35	0.38
b2	1.97	2.00	2.03
D	3.47	3.50	3.53
Е	1.87	1.90	1.93
е	0.95 BSC		
e1	1.54 BSC		

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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